

С

Β4

B3

B2

Β1

SCES650D-APRIL 2006-REVISED MAY 2008

4-BIT BIDIRECTIONAL VOLTAGE-LEVEL TRANSLATOR WITH AUTOMATIC DIRECTION SENSING AND ±15-kV ESD PROTECTION

FEATURES

- 1.2 V to 3.6 V on A Port and 1.65 V to 5.5 V on B Port (V_{CCA} ≤ V_{CCB})
- V_{CC} Isolation Feature If Either V_{CC} Input Is at GND, All Outputs Are in the High-Impedance State
- OE Input Circuit Referenced to V_{CCA}
- Low Power Consumption, 5- μ A Max I_{CC}
- I_{off} Supports Partial-Power-Down Mode Operation
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II

- ESD Protection Exceeds JESD 22
 - A Port
 - 2500-V Human-Body Model (A114-B)
 - 200-V Machine Model (A115-A)
 - 1500-V Charged-Device Model (C101)
 - B Port

2

1

- ±15-kV Human-Body Model (A114-B)
- 200-V Machine Model (A115-A)
- 1500-V Charged-Device Model (C101)

TERMINAL ASSIGNMENTS

(GXU/ZXU Package)

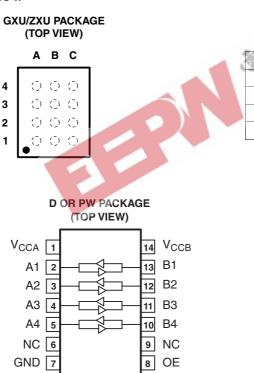
в

GND

OE

V_{CCA}

V_{CCB}





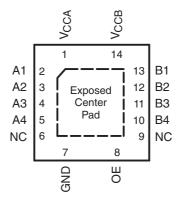
A

Α4

A3

A2

A1



N.C. - No internal connection

For RGY, if the exposed center pad is used it must only be connected to as a secondary ground or left electrically open.

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet. NanoFree is a trademark of Texas Instruments.



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	ZT PACKAG (TOP VIEW)	E
	321	
D C B A		

TERMINAL	ASSIGNMENTS
(YZT	Package)

	3	2	1
D	A4	GND	B4
С	A3	OE	B3
В	A2	V _{CCA}	B2
Α	A1	V _{CCB}	B1

DESCRIPTION/ORDERING INFORMATION

This 4-bit noninverting translator uses two separate configurable power-supply rails. The A port is designed to track V_{CCA}. V_{CCA} accepts any supply voltage from 1.2 V to 3.6 V. The B port is designed to track V_{CCB}. V_{CCB} accepts any supply voltage from 1.65 V to 5.5 V. This allows for universal low-voltage bidirectional translation between any of the 1.2-V, 1.5-V, 1.8-V, 2.5-V, 3.3-V, and 5-V voltage nodes. V_{CCA} should not exceed V_{CCB}.

When the output-enable (OE) input is low, all outputs are placed in the high-impedance state. To ensure the high-impedance state during power up or power down, OE should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

The TXB0104 is designed so that the OE input circuit is supplied by V_{CCA}.

This device is fully specified for partial-power-down applications using I_{off}. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

T _A	PACKAGE ⁽¹⁾⁽²⁾		ORDERABLE PART NUMBER	TOP-SIDE MARKING ⁽³⁾	
	NanoFree™ — WCSP (DSBGA) 0.23-mm Large Bump - YZT (Pb-free) 0.625-mm max height	Reel of 3000	TXB0104YZTR	2K7	
	UFBGA – GXU	Reel of 2500	TXB0104GXUR	YE04	
	UFBGA – ZXU (Pb-Free)	Reel of 2500	TXB0104ZXUR	YE04	
	QFN – RGY	Reel of 1000	TXB0104RGYR	YE04	
–40°C to 85°C	QFN - KGT	Reel 01 1000	TXB0104RGYRG4	1004	
		Tube of 50	TXB0104D		
			TXB0104DG4		
	SOIC – D	Reel of 2500	TXB0104DR	170104	
		Reel 01 2500	TXB0104DRG4		
	TSSOP – PW	Reel of 2000	TXB0104PWR	YE04	
	1330F - FW	Reel 01 2000	TXB0104PWRG4	I EU4	

ORDERING INFORMATION

(1) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.

(2) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.

(3) YZT: The actual top-side marking has three preceding characters to denote year, month, amd sequence code, and one following character to designate the assembly/test site. Pin 1 identifier indicates solder-bump composition (1 = SnPb, • = Pb-free).



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	PIN DESCRIPTION										
PIN NO.	BALL	NO.		FUNCTION							
D, PW, OR RGY	GXU/ZXU	YZT	NAME	FUNCTION							
1	B2	B2	V _{CCA}	A-port supply voltage 1.2 V \leq V _{CCA} \leq 3.6 V and V _{CCA} \leq V _{CCB} .							
2	A1	A3	A1	Input/output 1. Referenced to V _{CCA} .							
3	A2	B3	A2	Input/output 2. Referenced to V _{CCA} .							
4	A3	C3	A3	Input/output 3. Referenced to V _{CCA} .							
5	A4	D3	A4	Input/output 4. Referenced to V _{CCA} .							
6			NC	No connection. Not internally connected.							
7	B4	D2	GND	Ground							
8	B3	C2	OE	3-state output-mode enable. Pull OE low to place all outputs in 3-state mode. Referenced to $V_{\text{CCA}}.$							
9			NC	No connection. Not internally connected.							
10	C4	D1	B4	Input/output 4. Referenced to V _{CCB} .							
11	C3	C1	B3	Input/output 3. Referenced to V _{CCB} .							
12	C2	B1	B2	Input/output 2. Referenced to V _{CCB} .							
13	C1	A1	B1	Input/output 1. Referenced to V _{CCB} .							
14	B1	A2	V _{CCB}	B-port supply voltage 1.65 V \leq V _{CCB} \leq 5.5 V.							

	14	B1	A2	V _{CCB}	B-port s	upply voltage 1.65 V ≤ V	_{CCB} ≤ 5.5 V.			
		MAXIMUM RA		ss otherwise	noted)	upply voltage 1.65 V ≤ V				
							MIN	MAX	UNIT	
V _{CCA}	Supply	voltago rongo					-0.5	4.6	V	
V _{CCB}	Supply	voltage range					-0.5	6.5	v	
V	looutu					A port	-0.5	4.6	V	
VI	input v	oltage range				B port	-0.5	6.5		
V	Voltage	e range applied to	any output in the	e high-impedar	nce or	A port	-0.5	4.6	V	
Vo		off state				B port	-0.5	6.5	v	
V	Voltog	e range applied to	any output in the	high or low o	toto ⁽²⁾	A port	-0.5	$V_{CCA} + 0.5$		
Vo	voltage	e range applied to	any output in the	e nign of low s	lale	B port	-0.5	V _{CCB} + 0.5	V	
I _{IK}	Input c	lamp current				V ₁ < 0		-50	mA	
I _{OK}	Output	clamp current				V _O < 0		-50	mA	
lo	Continuous output current							±50	mA	
	Continu	uous current throug	gh V _{CCA} , V _{CCB} , c	or GND				±100	mA	
T _{stg}	Storage	e temperature rang	le				-65	150	°C	

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating" (2) The value of V_{CCA} and V_{CCB} are provided in the recommended operating conditions table.

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THERMAL IMPEDANCE RATINGS

		UNIT
θ_{JA} Package thermal impedance	D package ⁽¹⁾ 86	
	GXU/ZXU package ⁽¹⁾ 129	
	PW package ⁽¹⁾ 113	°C/W
	RGY package ⁽²⁾ 47	
	YZT package 90	
	Package thermal impedance	Package thermal impedance GXU/ZXU package ⁽¹⁾ 129 PW package ⁽¹⁾ 113 RGY package ⁽²⁾ 47

The package thermal impedance is calculated in accordance with JESD 51-7.
The package thermal impedance is calculated in accordance with JESD 51-5.

RECOMMENDED OPERATING CONDITIONS⁽¹⁾⁽²⁾

			V _{CCA}	V _{CCB}	MIN	МАХ	UNIT
V_{CCA}	Supply voltage				1.2	3.6	V
V _{CCB}	Supply voltage				1.65	5.5	v
V	High-level input voltage	Data inputs	1.2 V to 3.6 V	1.65 V to 5.5 V	$V_{CCI} \times 0.65^{(3)}$	V _{CCI}	V
VIH	nigh-level liput voltage	OE	1.2 V to 3.6 V	1.65 V to 5.5 V	$V_{CCA} imes 0.65$	5.5	v
V		Data inputs	1.2 V to 5.5 V	1.65 V to 5.5 V	0	$V_{CCI} \times 0.35^{(3)}$	V
VIL	Low-level input voltage	OE	1.2 V to 3.6 V	1.65 V to 5.5 V	0	$V_{CCA} {\times} 0.35$	v
	Voltage range applied to any	A-port		3 3ª	0	3.6	
Vo	output in the high-impedance or power-off state	B-port	1.2 V to 3.6 V	1.65 V to 5.5 V	0	5.5	V
		A-port inputs	1.2 V to 3.6 V	1.65 V to 5.5 V		40	
Δt/Δv	Input transition rise or fall rate	P port inputo	1.2 V to 3.6 V	1.65 V to 3.6 V		40	ns/V
		B-port inputs	1.2 V 10 3.6 V	4.5 V to 5.5 V		30	
T _A	Operating free-air temperature				-40	85	°C

(1) The A and B sides of an unused data I/O pair must be held in the same state, i.e., both at V_{CCI} or both at GND. (2) V_{CCA} must be less than or equal to V_{CCB} and must not exceed 3.6 V. (3) V_{CCI} is the supply voltage associated with the input port.



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ELECTRICAL CHARACTERISTICS⁽¹⁾⁽²⁾

over recommended operating free-air temperature range (unless otherwise noted)

п	ARAMETER	TEST CONDITIONS	М	V	T _A = 25°C	–40°C to 85°C	UNIT	
P		TEST CONDITIONS	V _{CCA}	V _{CCB}	MIN TYP MAX	MIN MAX	UNIT	
		L 00 ··· A	1.2 V		1.1		v	
V _{OHA}		I _{OH} = -20 μA	1.4 V to 3.6 V			V _{CCA} - 0.4	V	
		1 00 4	1.2 V		0.9		v	
V _{OLA}		I _{OL} = 20 μA	1.4 V to 3.6 V			0.4	V	
V _{OHB}		I _{OH} = -20 μA		1.65 V to 5.5 V		V _{CCB} - 0.4	V	
V _{OLB}		I _{OL} = 20 μA		1.65 V to 5.5 V		0.4	V	
l _l	OE	$V_I = V_{CCI}$ or GND	1.2 V to 3.6 V	1.65 V to 5.5 V	±1	±2	μA	
	A port	V_{I} or V_{O} = 0 to 3.6 V	0 V	0 V to 5.5 V	±1	±2		
l _{off}	B port	$V_{\rm I}$ or $V_{\rm O}$ = 0 to 5.5 V	0 V to 3.6 V	0 V	±1	±2	μA	
I _{OZ}	A or B port	OE = GND	1.2 V to 3.6 V	1.65 V to 5.5 V	±1	±2	μA	
			1.2 V	1.65 V to 5.5 V	0.06			
		$V_{I} = V_{CCI}$ or GND,	1.4 V to 3.6 V	1.65 V to 5.5 V		5		
I _{CCA}		$I_0 = 0$	3.6 V	0 V	-	2	μA	
			0 V	5.5 V 🍕	14 14	-2	-	
			1.2 V	1.65 V to 5.5 V	3.4			
		$V_{I} = V_{CCI}$ or GND,	1.4 V to 3.6 V	1.65 V to 5.5 V		5		
I _{CCB}		$I_0 = 0$	3.6 V	V 0.		-2	μA	
			0 V	5.5 V		2	-	
		$V_{I} = V_{CCI}$ or GND,	1.2 V	1.65 V to 5.5 V	3.5			
I _{CCA} +	ICCB	$I_0 = 0$	1.4 V to 3.6 V	1.65 V to 5.5 V		10	μA	
		$V_{I} = V_{CCI}$ or GND,	1.2 V	1.65 V to 5.5 V	0.05			
I _{CCZA}		$I_0 = 0,$ OE = GND	1.4 V to 3.6 V	1.65 V to 5.5 V		5	μA	
		$V_{I} = V_{CCI}$ or GND,	1.2 V	1.65 V to 5.5 V	3.3			
I _{CCZB}		l _O = 0, OE = GND	1.4 V to 3.6 V	1.65 V to 5.5 V		5	μA	
Ci	OE		1.2 V to 3.6 V	1.65 V to 5.5 V	3	4	pF	
A port 5		6						
C _{io}	B port		1.2 V to 3.6 V	1.65 V to 5.5 V	11	14	pF	

 $\begin{array}{ll} \mbox{(1)} & V_{CCI} \mbox{ is the supply voltage associated with the input port.} \\ \mbox{(2)} & V_{CCO} \mbox{ is the supply voltage associated with the output port.} \end{array}$

TEXAS INSTRUMENTS

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TIMING REQUIREMENTS

 $T_A = 25^{\circ}C, V_{CCA} = 1.2 V$

			V _{CCB} = 1.8 V	V _{CCB} = 2.5 V	V _{CCB} = 3.3 V	$V_{CCB} = 5 V$	UNIT
			TYP	TYP	TYP	TYP	UNIT
	Data rate		20	20	20	20	Mbps
tw	Pulse duration	Data inputs	50	50	50	50	ns

TIMING REQUIREMENTS

over recommended operating free-air temperature range, $V_{CCA} = 1.5 \text{ V} \pm 0.1 \text{ V}$ (unless otherwise noted)

			V _{CCB} = ± 0.1		V _{CCB} = ± 0.2		V _{CCB} = ± 0.3		V _{CCB} = ± 0.5		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
	Data rate			40		40		40		40	Mbps
tw	Pulse duration	Data inputs	25		25		25		25		ns

TIMING REQUIREMENTS

over recommended operating free-air temperature range, $V_{CCA} = 1.8 \text{ V} \pm 0.15 \text{ V}$ (unless otherwise noted)

			V _{CCB} = 1.8 V ± 0.15 V				V _{CCB} = 3.3 V ± 0.3 V		V _{CCB} = 5 V ± 0.5 V		UNIT
			MIN	MAX	MIN	MAX	MIN MIN	MAX	MIN	MAX	
	Data rate		-	60	1	60		60		60	Mbps
tw	Pulse duration	Data inputs	17	C	17		17		17		ns

TIMING REQUIREMENTS

over recommended operating free-air temperature range, V_{CCA} = 2.5 V ± 0.2 V (unless otherwise noted)

			V _{CCB} = 2.5 V ± 0.2 V		V _{CCB} = 3.3 V ± 0.3 V		V _{CCB} = 5 V ± 0.5 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
	Data rate			100		100		100	Mbps
tw	Pulse duration	Data inputs	10		10		10		ns

TIMING REQUIREMENTS

over recommended operating free-air temperature range, V_{CCA} = 3.3 V ± 0.3 V (unless otherwise noted)

			V _{CCB} = 3 ± 0.3	.3 V V	V _{CCB} = 5 ± 0.5 V	5 V V	UNIT
			MIN	MAX	MIN	MAX	
	Data rate			100		100	Mbps
t _w	Pulse duration	Data inputs	10		10		ns



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SWITCHING CHARACTERISTICS

 $T_A = 25^{\circ}C, \ V_{CCA} = 1.2 \ V$

PARAMETER	FROM	то	V _{CCB} = 1.8 V	V _{CCB} = 2.5 V	V _{CCB} = 3.3 V	$V_{CCB} = 5 V$	
PARAMETER	(INPUT)	(OUTPUT)	ТҮР	ТҮР	ТҮР	TYP	UNIT
	А	В	6.9	5.7	5.3	5.5	
t _{pd}	В	А	7.4	6.4	6	5.8	ns
	OE	А	1	1	1	1	
t _{en}	ÛE	В	1	1	1	1	μs
		А	18	15	14	14	
t _{dis}	OE	В	20	17	16	16	ns
t _{rA} , t _{fA}	A-port rise a	ind fall times	4.2	4.2	4.2	4.2	ns
t _{rB} , t _{fB}	B-port rise a	ind fall times	2.1	1.5	1.2	1.1	ns
t _{SK(O)}	Channel-to-c	hannel skew	0.4	0.5	0.5	1.4	ns
Max data rate			20	20	20	20	Mbps

SWITCHING CHARACTERISTICS

over recommended operating free-air temperature range, V_{CCA} = 1.5 V ± 0.1 V (unless otherwise noted)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CCB} = ± 0.1		V _{CCB} = ± 0.2		V _{CCB} = ± 0.3		V _{ССВ} = ± 0.5		UNIT
	(INPOT)	(001701)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
	А	В	1.4	12.9	1.2	10.1	1.1	10	0.8	9.9	
t _{pd}	В	A	0.9	14.2	0.7	12	0.4	11.7	0.3	13.7	ns
	OE	А		1		1		1		1	
t _{en}	OL	В		1		1		1		1	μs
	05	A	5.9	31	5.7	25.9	5.6	23	5.7	22.4	
t _{dis}	OE	В	5.4	30.3	4.9	22.8	4.8	20	4.9	19.5	ns
t _{rA} , t _{fA}	A-port rise a	and fall times	1.4	5.1	1.4	5.1	1.4	5.1	1.4	5.1	ns
t _{rB} , t _{fB}	B-port rise a	ind fall times	0.9	4.5	0.6	3.2	0.5	2.8	0.4	2.7	ns
t _{SK(O)}	Channel-to-c	hannel skew		0.5		0.5		0.5		0.5	ns
Max data rate			40		40		40		40		Mbps

SWITCHING CHARACTERISTICS

over recommended operating free-air temperature range, V_{CCA} = 1.8 V ± 0.15 V (unless otherwise noted)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CCB} = ± 0.1		V _{CCB} = ± 0.2		V _{CCB} = ± 0.3		V _{ССВ} = ± 0.5		UNIT	
	(INPOT)	(001201)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX		
	А	В	1.6	11	1.4	7.7	1.3	6.8	1.2	6.5		
t _{pd}	В	A	1.5	12	1.3	8.4	1	7.6	0.9	7.1	ns	
	OE	A		1		1		1		1		
t _{en}	UE	0E	В		1		1		1		1	μs
	OE		А	5.9	31	5.1	21.3	5	19.3	5	17.4	
t _{dis}		В	5.4	30.3	4.4	20.8	4.2	17.9	4.3	16.3	ns	
t _{rA} , t _{fA}	A-port rise a	and fall times	1	4.2	1.1	4.1	1.1	4.1	1.1	4.1	ns	
t _{rB} , t _{fB}	B-port rise a	and fall times	0.9	3.8	0.6	3.2	0.5	2.8	0.4	2.7	ns	
t _{SK(O)}	Channel-to-c	channel skew		0.5		0.5		0.5		0.5	ns	
Max data rate			60		60		60		60		Mbps	



SWITCHING CHARACTERISTICS

over recommended operating free-air temperature range, $V_{CCA} = 2.5 \text{ V} \pm 0.2 \text{ V}$ (unless otherwise noted)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CCB} = ± 0.2		V _{CCB} = ± 0.3		V _{CCB} = ± 0.5	5 V V	UNIT
	(INFUT)	(001201)	MIN	MAX	MIN	MAX	MIN	MAX	
+	А	В	1.1	6.3	1	5.2	0.9	4.7	20
t _{pd}	В	А	1.2	6.6	1.1	5.1	0.9	4.4	ns
	OE	А		1		1		1	
t _{en}	ÛE	В		1		1		1	μs
	OE	А	5.1	21.3	4.6	15.2	4.6	13.2	~~
t _{dis}		В	4.4	20.8	3.8	16	3.9	13.9	ns
t _{rA} , t _{fA}	A-port rise a	ind fall times	0.8	3	0.8	3	0.8	3	ns
t _{rB} , t _{fB}	B-port rise a	ind fall times	0.7	2.6	0.5	2.8	0.4	2.7	ns
t _{SK(O)}	Channel-to-c	hannel skew		0.5		0.5		0.5	ns
Max data rate			100		100		100		Mbps

SWITCHING CHARACTERISTICS

over recommended operating free-air temperature range, V_{CCA} = 3.3 V \pm 0.3 V (unless otherwise noted)

PARAMETER	FROM					8.3 V V	V _{CCB} = ± 0.5	UNIT	
	(INPUT)				MIN	MAX	MIN	MAX	
	А		В	G	0.9	4.7	0.8	4	
t _{pd}	В		А		1	4.9	0.9	3.8	ns
	OE		A			1		1	
t _{en}	0E		В			1		1	μs
			Α		4.6	15.2	4.3	12.1	
t _{dis}	OE		В		3.8	16	3.4	13.2	ns
t _{rA} , t _{fA}	A-port rise a	and fall time	s		0.7	2.5	0.7	2.5	ns
t _{rB} , t _{fB}	B-port rise a	and fall time	s		0.5	2.1	0.4	2.7	ns
t _{SK(O)}	Channel-to-o	channel ske	w			0.5		0.5	ns
Max data rate					100		100		Mbps



TXB0104

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OPERATING CHARACTERISTICS

 $T_A = 25^{\circ}C$

						V _{CCA}					
			1.2 V	1.2 V	1.5 V	1.8 V	2.5 V	2.5 V	3.3 V		
			V _{CCB}								
PARAMETER		TEST CONDITIONS	5 V	1.8 V	1.8 V	1.8 V	2.5 V	5 V	3.3 V to 5 V	UNIT	
			TYP	TYP	TYP	TYP	TYP	TYP	TYP		
<u> </u>	A-port input, B-port output	$C_1 = 0, f = 10 \text{ MHz},$	7.8	10	9	8	8	8	9		
C _{pdA}	B-port input, A-port output	$t_r = t_f = 1 \text{ ns},$	12	11	11	11	11	11	1 11	~F	
C	A-port input, B-port output	$OE = V_{CCA}$	38.1	28	28	28	29	29	29	pF	
C _{pdB}	B-port input, A-port output	(outputs enabled)	25.4	19	18	18	19	21	22		
~	A-port input, B-port output	$C = 0.5 = 10 MH_{7}$	0.01	0.01	0.01	0.01	0.01	0.01	0.01		
C_{pdA}	B-port input, A-port output	$C_{L} = 0, f = 10 \text{ MHz},$ $t_{r} = t_{f} = 1 \text{ ns},$	0.01	0.01	0.01	0.01	0.01	0.01	0.01	~ -	
C	A-port input, B-port output	OE = GND	0.01	0.01	0.01	0.01	0.01	0.01	0.03	pF	
C _{pdB}	B-port input, A-port output	(outputs disabled)	0.01	0.01	0.01	0.01	0.01	0.01	0.04		

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PRINCIPLES OF OPERATION

Applications

The TXB0104 can be used in level-translation applications for interfacing devices or systems operating at different interface voltages with one another.

Architecture

The TXB0104 architecture (see Figure 1) does not require a direction-control signal to control the direction of data flow from A to B or from B to A. In a dc state, the output drivers of the TXB0104 can maintain a high or low, but are designed to be weak, so that they can be overdriven by an external driver when data on the bus starts flowing the opposite direction.

The output one shots detect rising or falling edges on the A or B ports. During a rising edge, the one shot turns on the PMOS transistors (T1, T3) for a short duration, which speeds up the low-to-high transition. Similarly, during a falling edge, the one shot turns on the NMOS transistors (T2, T4) for a short duration, which speeds up the high-to-low transition. The typical output impedance during output transition is 70 Ω at V_{CCO} = 1.2 V to 1.8 V, 50 Ω at V_{CCO} = 1.8 V to 3.3 V, and 40 Ω at V_{CCO} = 3.3 V to 5 V.

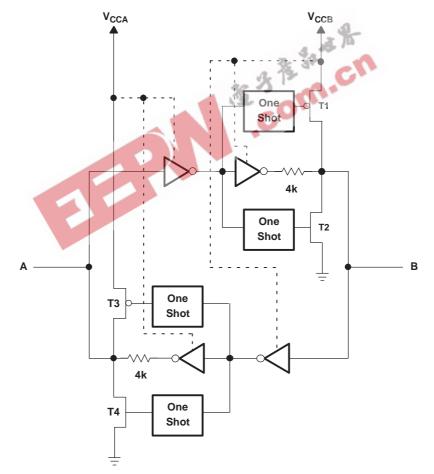
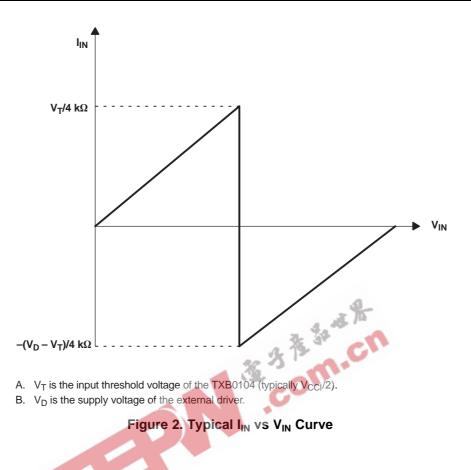


Figure 1. Architecture of TXB0104 I/O Cell

Input Driver Requirements

Typical I_{IN} vs V_{IN} characteristics of the TXB0104 are shown in Figure 2. For proper operation, the device driving the data I/Os of the TXB0104 must have drive strength of at least ±2 mA.

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Power Up

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During operation, ensure that $V_{CCA} \leq V_{CCB}$ at all times. During power-up sequencing, $V_{CCA} \geq V_{CCB}$ does not damage the device, so any power supply can be ramped up first. The TXB0104 has circuitry that disables all output ports when either V_{CC} is switched off ($V_{CCA/B} = 0$ V).

Enable and Disable

The TXB0104 has an OE input that is used to disable the device by setting OE = low, which places all I/Os in the high-impedance (Hi-Z) state. The disable time (t_{dis}) indicates the delay between when OE goes low and when the outputs acutally get disabled (Hi-Z). The enable time (t_{en}) indicates the amount of time the user must allow for the one-shot circuitry to become operational after OE is taken high.

Pullup or Pulldown Resistors on I/O Lines

The TXB0104 is designed to drive capacitive loads of up to 70 pF. The output drivers of the TXB0104 have low dc drive strength. If pullup or pulldown resistors are connected externally to the data I/Os, their values must be kept higher than 50 k Ω to ensure that they do not contend with the output drivers of the TXB0104.

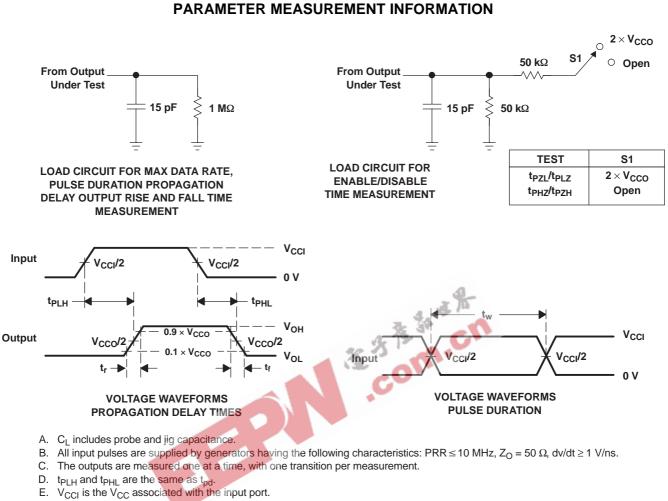
For the same reason, the TXB0104 should not be used in applications such as I^2C or 1-Wire where an open-drain driver is connected on the bidirectional data I/O. For these applications, use a device from the TI TXS01xx series of level translators.

TXB0104

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- F. V_{CCO} is the V_{CC} associated with the output port.
- G. All parameters and waveforms are not applicable to all devices.

Figure 3. Load Circuits and Voltage Waveforms



PACKAGE OPTION ADDENDUM

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PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	e Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
TXB0104D	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TXB0104DG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TXB0104DR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TXB0104DRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TXB0104GXUR	ACTIVE	BGA MI CROSTA R JUNI OR	GXU	12	2500	TBD	SNPB	Level-1-240C-UNLIM
TXB0104PWR	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TXB0104PWRG4	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TXB0104RGYR	ACTIVE	QFN	RGY	14	1000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TXB0104RGYRG4	ACTIVE	QFN	RGY	14	1000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
TXB0104YZTR	ACTIVE	DSBGA	YZT	12	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM
TXB0104ZXUR	ACTIVE	BGA MI CROSTA R JUNI OR	ZXU	12	2500	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details. **TBD:** The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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OTHER QUALIFIED VERSIONS OF TXB0104 :

Automotive: TXB0104-Q1

NOTE: Qualified Version Definitions:

• Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

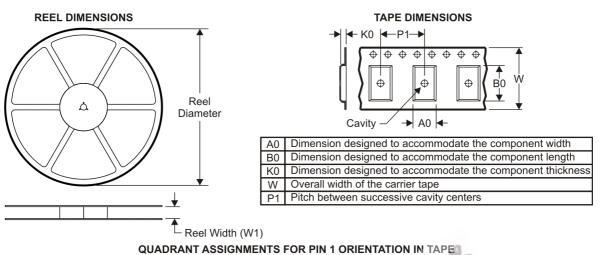


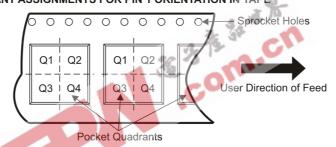


PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION



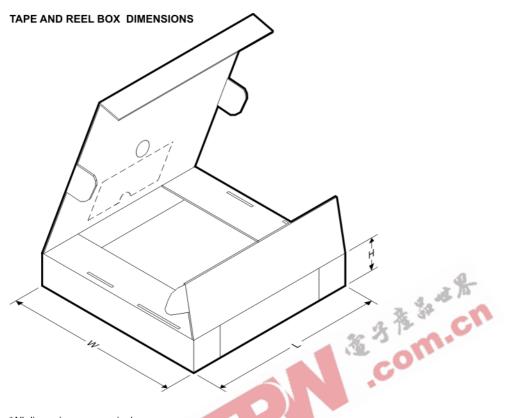


*All dimensions are nominal												
Device		Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadra
TXB0104DR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TXB0104GXUR	BGA MI CROSTA R JUNI OR	GXU	12	2500	330.0	8.4	2.3	2.8	1.0	4.0	8.0	Q2
TXB0104PWR	TSSOP	PW	14	2000	330.0	12.4	7.0	5.6	1.6	8.0	12.0	Q1
TXB0104RGYR	QFN	RGY	14	1000	180.0	12.4	3.85	3.85	1.35	8.0	12.0	Q1
TXB0104YZTR	DSBGA	YZT	12	3000	180.0	8.4	1.5	2.03	0.7	4.0	8.0	Q2
TXB0104ZXUR	BGA MI CROSTA R JUNI OR	ZXU	12	2500	330.0	8.4	2.3	2.8	1.0	4.0	8.0	Q2



PACKAGE MATERIALS INFORMATION

17-Jul-2008



*All dimensions are nomina	
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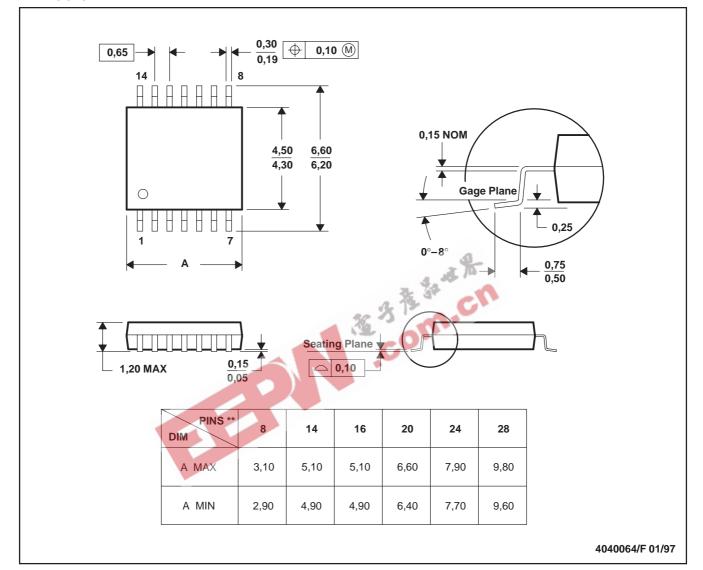
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TXB0104DR	SOIC	D	14	2500	346.0	346.0	33.0
TXB0104GXUR	BGA MICROSTAR JUNIOR	GXU	12	2500	340.5	338.1	20.6
TXB0104PWR	TSSOP	PW	14	2000	346.0	346.0	29.0
TXB0104RGYR	QFN	RGY	14	1000	190.5	212.7	31.8
TXB0104YZTR	DSBGA	YZT	12	3000	220.0	220.0	34.0
TXB0104ZXUR	BGA MICROSTAR JUNIOR	ZXU	12	2500	340.5	338.1	20.6

MECHANICAL DATA

MTSS001C - JANUARY 1995 - REVISED FEBRUARY 1999

PLASTIC SMALL-OUTLINE PACKAGE





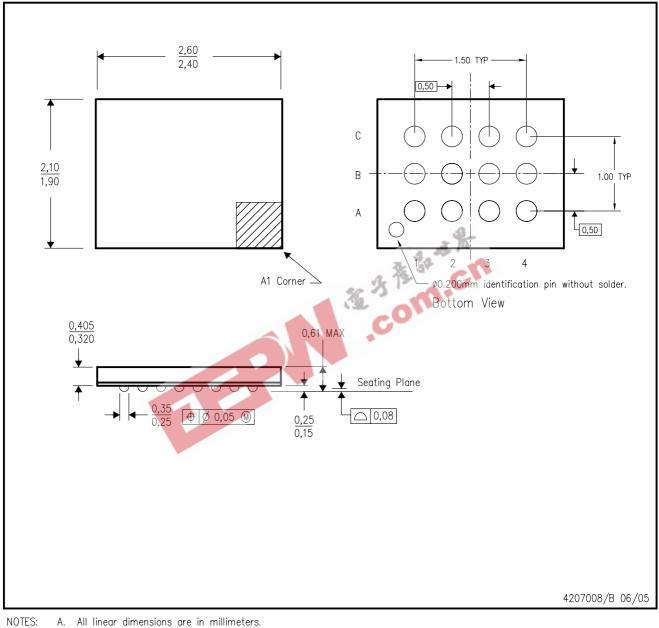
NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.
- D. Falls within JEDEC MO-153



GXU (S-PBGA-N12)

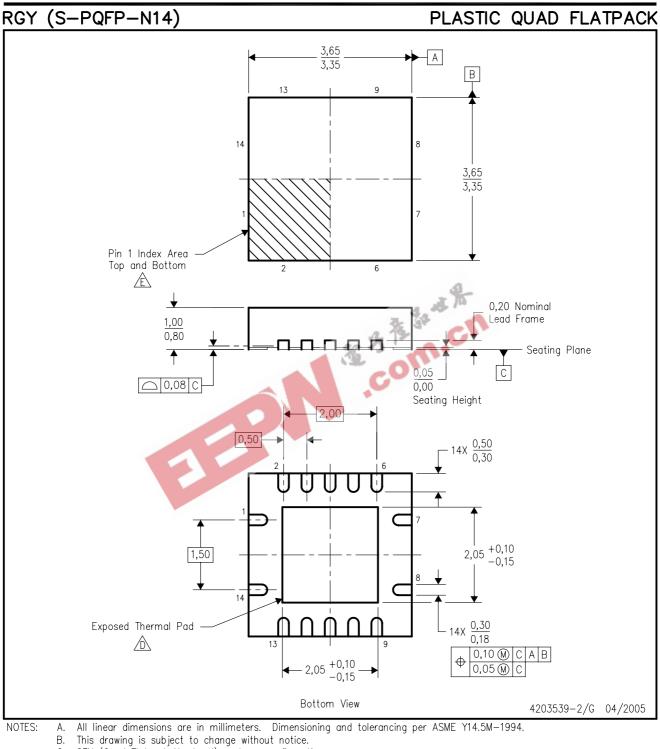
PLASTIC BALL GRID ARRAY



A. All linear dimensions are in millimeters.B. This drawing is subject to change without notice.



MECHANICAL DATA



- C. QFN (Quad Flatpack No-Lead) package configuration.
- A The package thermal pad must be soldered to the board for thermal and mechanical performance.
- Pin 1 identifiers are located on both top and bottom of the package and within the zone indicated. The Pin 1 identifiers are either a molded, marked, or metal feature.
- F. Package complies to JEDEC MO-241 variation BA.



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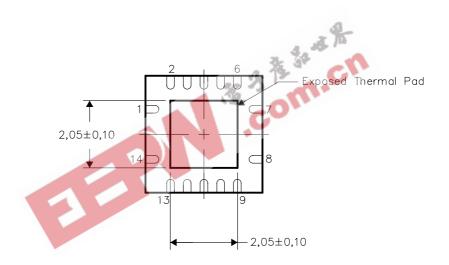
THERMAL PAD MECHANICAL DATA RGY (S-PQFP-N14)

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No-Lead (QFN) package and its advantages, refer to Application Report, Quad Flatpack No-Lead Logic Packages, Texas Instruments Literature No. SCBA017. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.

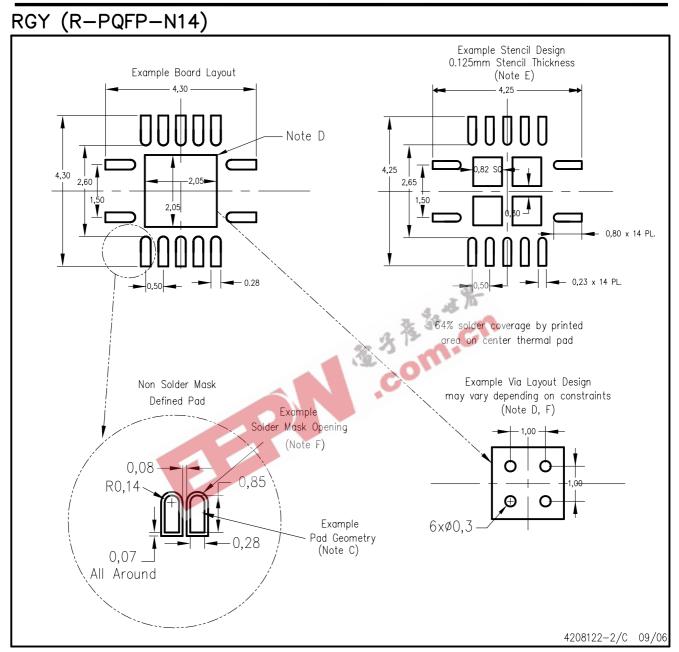


Bottom View

NOTE: All linear dimensions are in millimeters

Exposed Thermal Pad Dimensions

LAND PATTERN



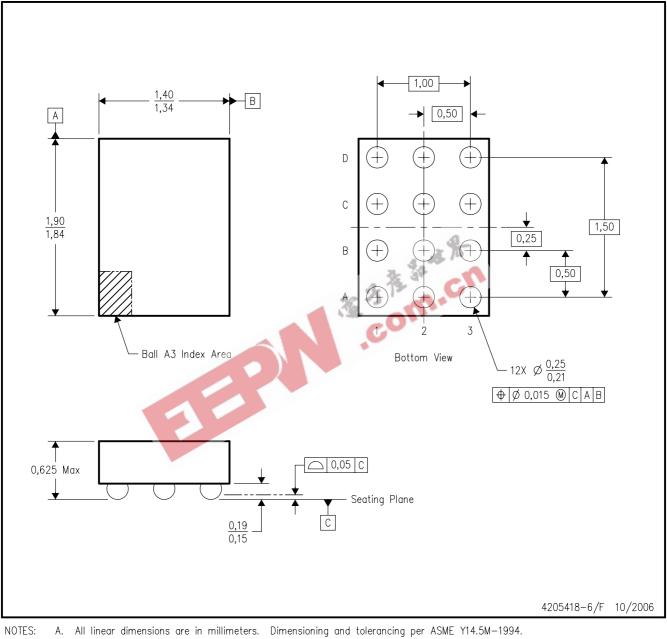
NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat-Pack Packages, Texas Instruments Literature No. SCBA017, SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com http://www.ti.com.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
- F. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.



YZT (R-XBGA-N12)

(CUSTOM) DIE-SIZE BALL GRID ARRAY



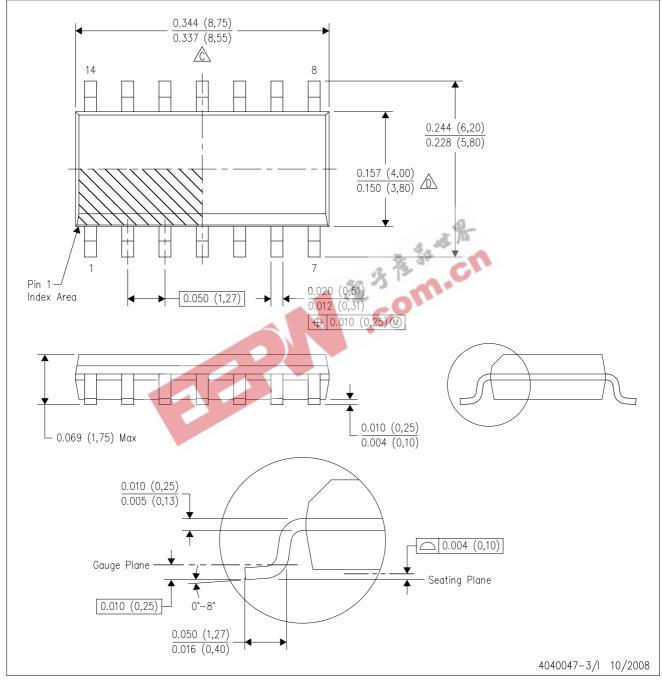
- B. This drawing is subject to change without notice.
- C. NanoFree™ package configuration.
- D. This is a lead-free solder ball design.

NanoFree is a trademark of Texas Instruments.



D (R-PDSO-G14)

PLASTIC SMALL-OUTLINE PACKAGE



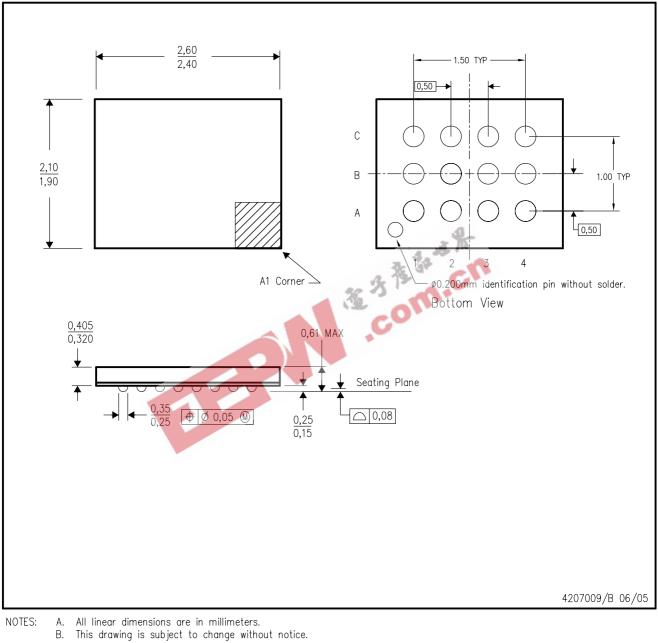
Α. NOTES: All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- 🖄 Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 (0,15) per end.
- Body width does not include interlead flash. Interlead flash shall not exceed .017 (0,43) per side. E. Reference JEDEC MS-012 variation AB.



ZXU (S-PBGA-N12)

PLASTIC BALL GRID ARRAY



- C. This package is a lead-free solder ball design.



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